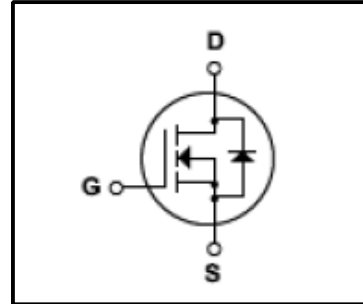


Silicon N-Channel MOSFET

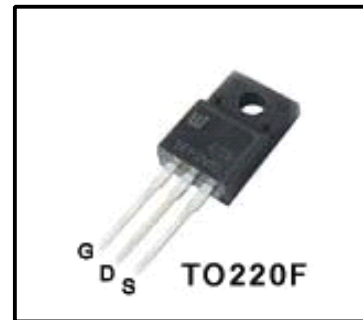
Features

- 7A,600V, $R_{DS(on)}$ (Max 1.2 Ω)@ $V_{GS}=10V$
- Ultra-low Gate Charge(Typical 29nC)
- Fast Switching Capability
- 100%Avalanche Tested
- Isolation Voltage($V_{ISO}=4000V$ AC)
- Maximum Junction Temperature Range(150℃)



General Description

This Power MOSFET is produced using Winsemi's advanced planar stripe,VDMOS technology. This latest technology has been especially designed to minimize on-state resistance,have a high rugged avalanche characteristics. This devices is specially well suited for half bridge and full bridge resonant topology line a electronic lamp ballast,high efficiency switched mode power supplies, active power factor correction.



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DSS}	Drain Source Voltage	600	V
I_D	Continuous Drain Current(@ $T_c=25^\circ C$)	7*	A
	Continuous Drain Current(@ $T_c=100^\circ C$)	4.1*	A
I_{DM}	Drain Current Pulsed (Note1)	26	A
V_{GS}	Gate to Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note2)	240	mJ
E_{AR}	Repetitive Avalanche Energy (Note1)	15	mJ
dv/dt	Peak Diode Recovery dv/dt (Note3)	4.5	V/ ns
P_D	Total Power Dissipation(@ $T_c=25^\circ C$)	48	W
	Derating Factor above $25^\circ C$	0.38	W/℃
T_J, T_{stg}	Junction and Storage Temperature	-55~150	℃
T_L	Channel Temperature	300	℃

*Drain current limited by junction temperature

Thermal Characteristics

Symbol	Parameter	Value			Units
		Min	Typ	Max	
R_{QJC}	Thermal Resistance , Junction -to -Case	-	-	2.6	℃/W
R_{QJA}	Thermal Resistance , Junction-to -Ambient	-	-	62.5	℃/W

Electrical Characteristics(Tc=25℃)

Characteristics		Symbol	Test Condition	Min	Type	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} =±30V,V _{DS} =0V	-	-	±100	nA
Gate-source breakdown voltage		V _{(BR)GSS}	I _G =±10 μA,V _{DS} =0V	±30	-	-	V
Drain cut -off current		I _{DSS}	V _{DS} =600V,V _{GS} =0V	-	-	10	μA
			V _{DS} =480V,Tc=125℃	-		100	μA
Drain -source breakdown voltage		V _{(BR)DSS}	I _D =250 μA,V _{GS} =0V	600	-	-	V
Gate threshold voltage		V _{GS(th)}	V _{DS} =10V,I _D =250 μA	2	-	4	V
Drain -source ON resistance		R _{DS(ON)}	V _{GS} =10V,I _D =3.5A	-	0.8	1.2	Ω
Forward Transconductance		g _{fs}	V _{DS} =50V,I _D =3.5A	-	8.7	-	S
Input capacitance		C _{iSS}	V _{DS} =25V, V _{GS} =0V, f=1MHz	-	1100	1430	pF
Reverse transfer capacitance		C _{rSS}		-	15	20	
Output capacitance		C _{oSS}		-	135	175	
Switching time	Rise time	t _r	V _{DD} =200V, I _D =7.0A, R _G =25Ω, (Note4,5)	-	30	70	ns
	Turn-on time	t _{on}		-	80	170	
	Fall time	t _f		-	65	140	
	Turn-off time	t _{off}		-	60	130	
Total gate charge(gate-source plus gate-drain)		Q _g	V _{DD} =480V, V _{GS} =10V, I _D =7.0A (Note4,5)	-	29	38	nC
Gate-source charge		Q _{gs}		-	7	-	
Gate-drain("miller") Charge		Q _{gd}		-	14.5	-	

Source-Drain Ratings and Characteristics(Ta=25℃)

Characteristics	Symbol	Test Condition	Min	Type	Max	Unit
Continuous drain reverse current	I _{DR}	-	-	-	7.0	A
Pulse drain reverse current	I _{DRP}	-	-	-	28	A
Forward voltage(diode)	V _{DSF}	I _{DR} =7.4A,V _{GS} =0V	-	-	1.4	V
Reverse recovery time	t _{rr}	I _{DR} =7.4A,V _{GS} =0V,	-	320	-	ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt =100 A / μs	-	2.4	-	μC

Note 1.Repeativity rating :pulse width limited by junction temperature

2.L=18.5mH I_{AS}=7A,V_{DD}=50V,R_G=0Ω ,Starting T_J=25℃

3.I_{SD}≤7.0A,di/dt≤200A/us,V_{DD}<BV_{DSS},STARTING T_J=25℃

4.Pulse Test:Pulse Width≤300us,Duty Cycles≤2%

5. Essentially independent of operating temperature.

This transistor is an electrostatic sensitive device

Please handle with caution

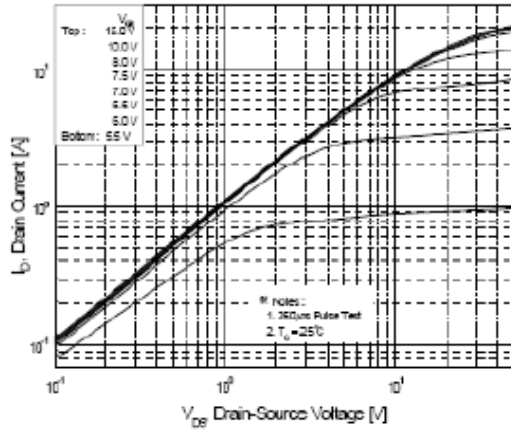


Fig.1 On-State Characteristics

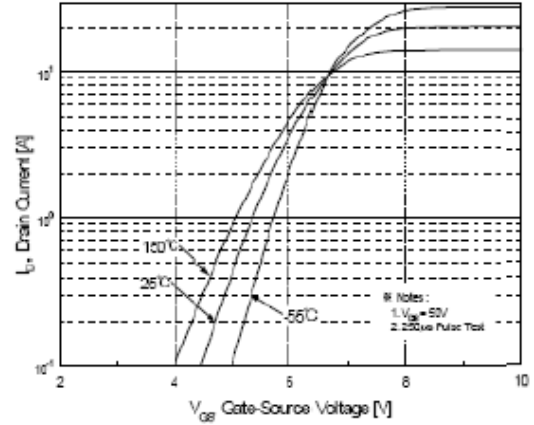


Fig.2 Transfer Current characteristics

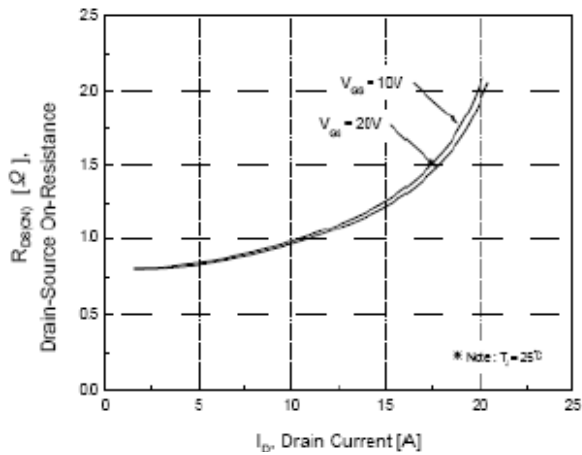


Fig.3 On Resistance variation vs Drain Current

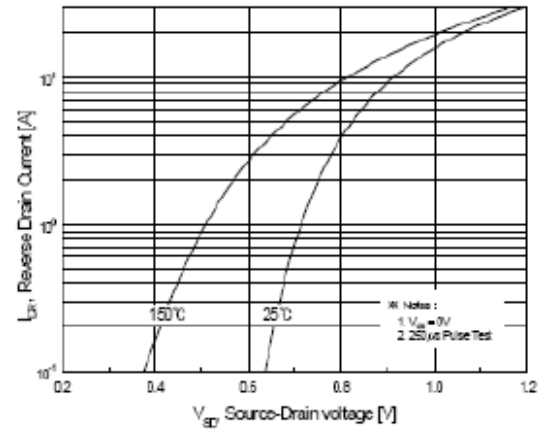


Fig.4 Body Diode Forward Voltage Variation with Source Current and temperature

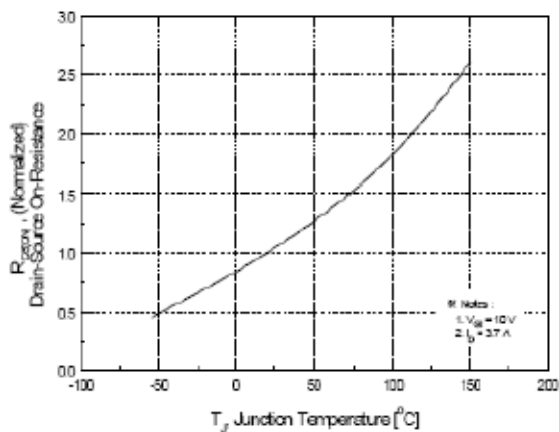


Fig.5 On-Resistance Variation vs Junction Temperature

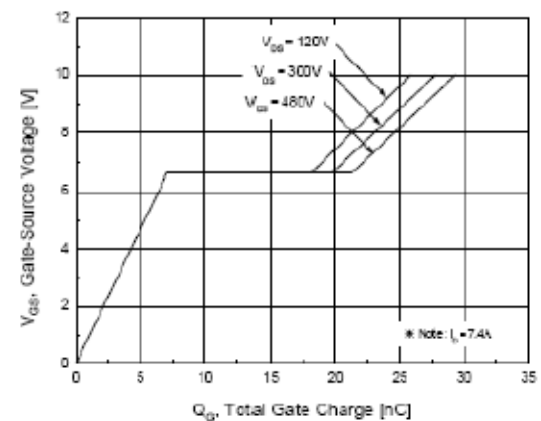
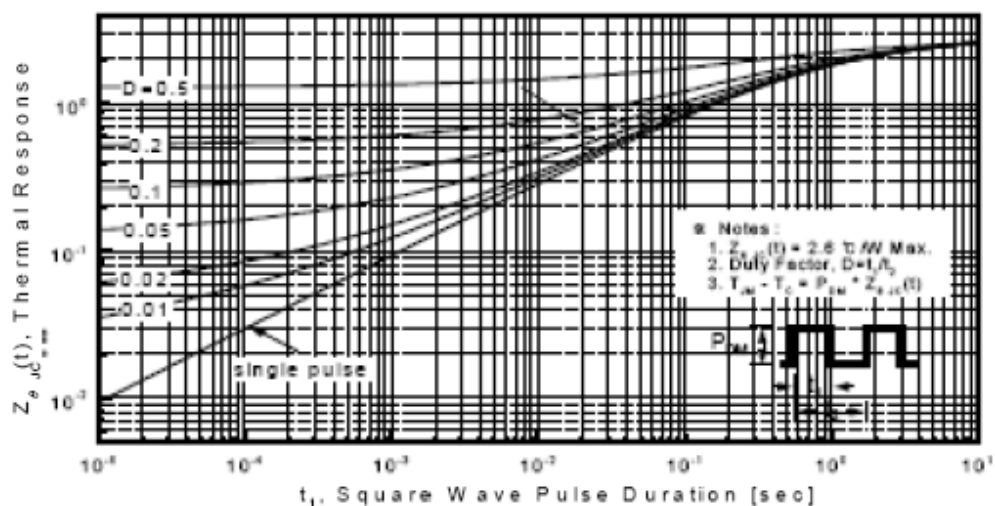
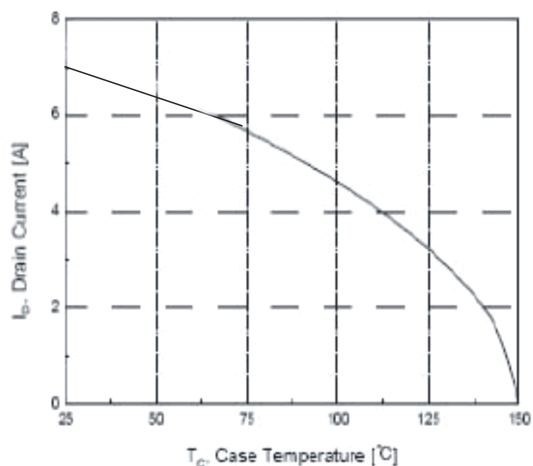
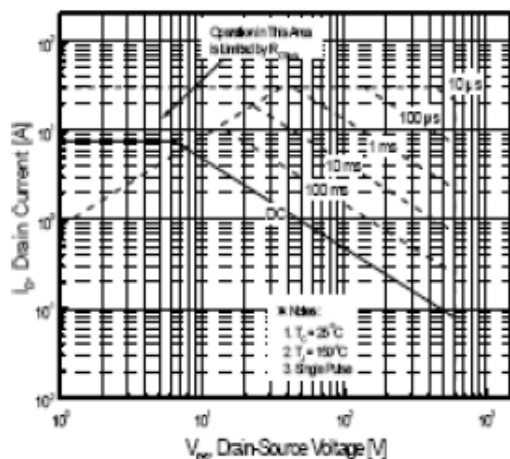


Fig.6 Gate Charge Characteristics



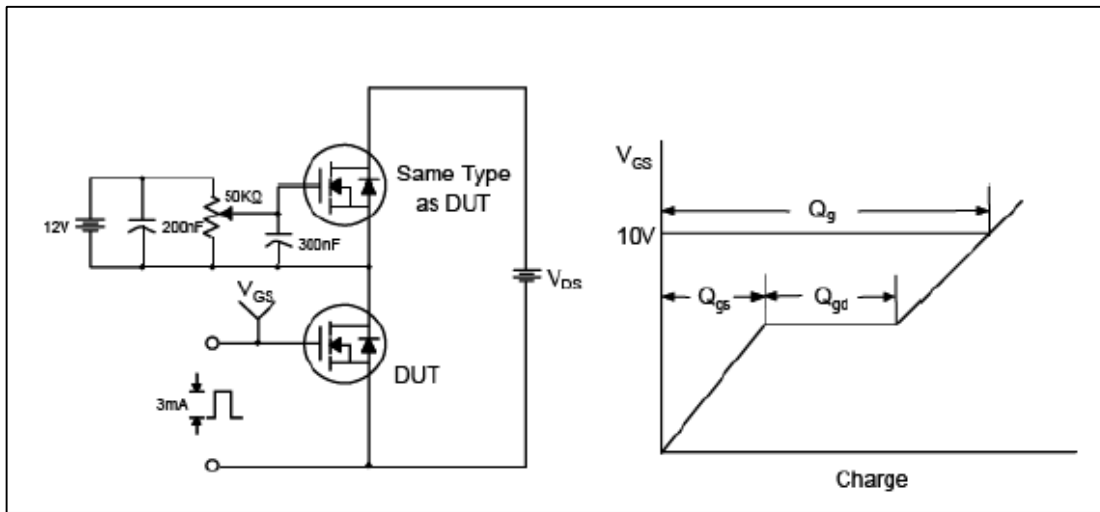


Fig.10 Gate Test circuit & Waveform

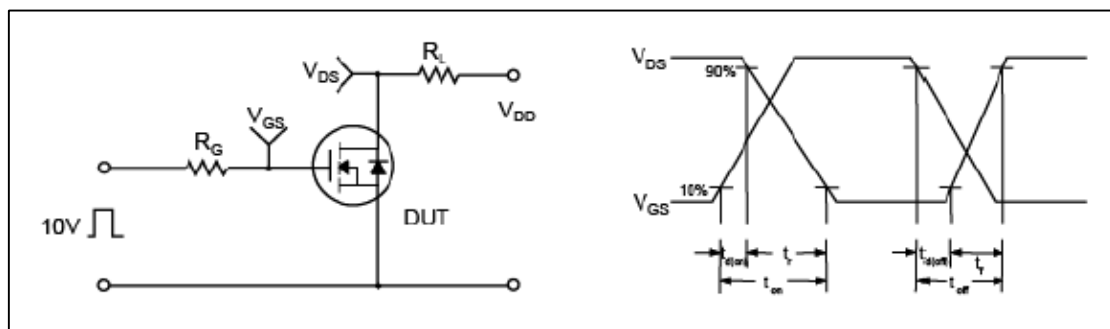


Fig.11 Resistive Switching Test Circuit & Waveform

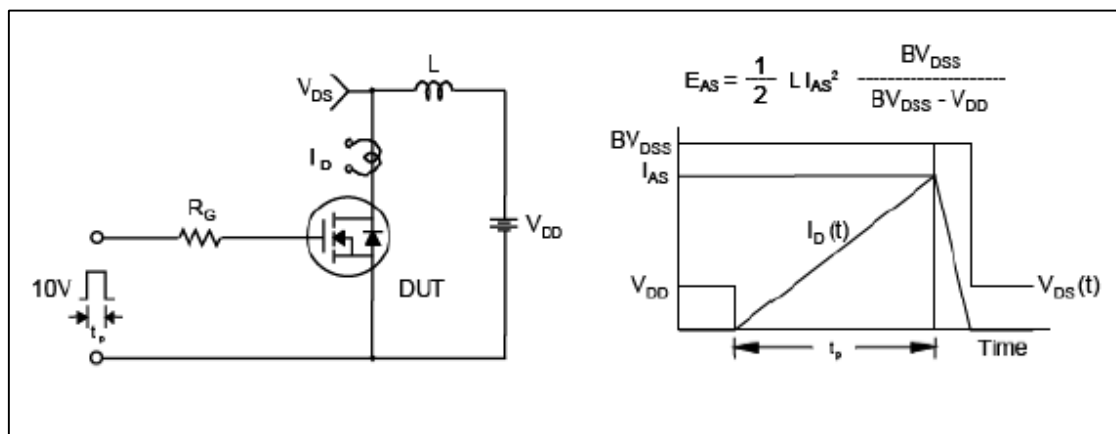


Fig.12 Uncamped Inductive Switching Test Circuit & Waveform

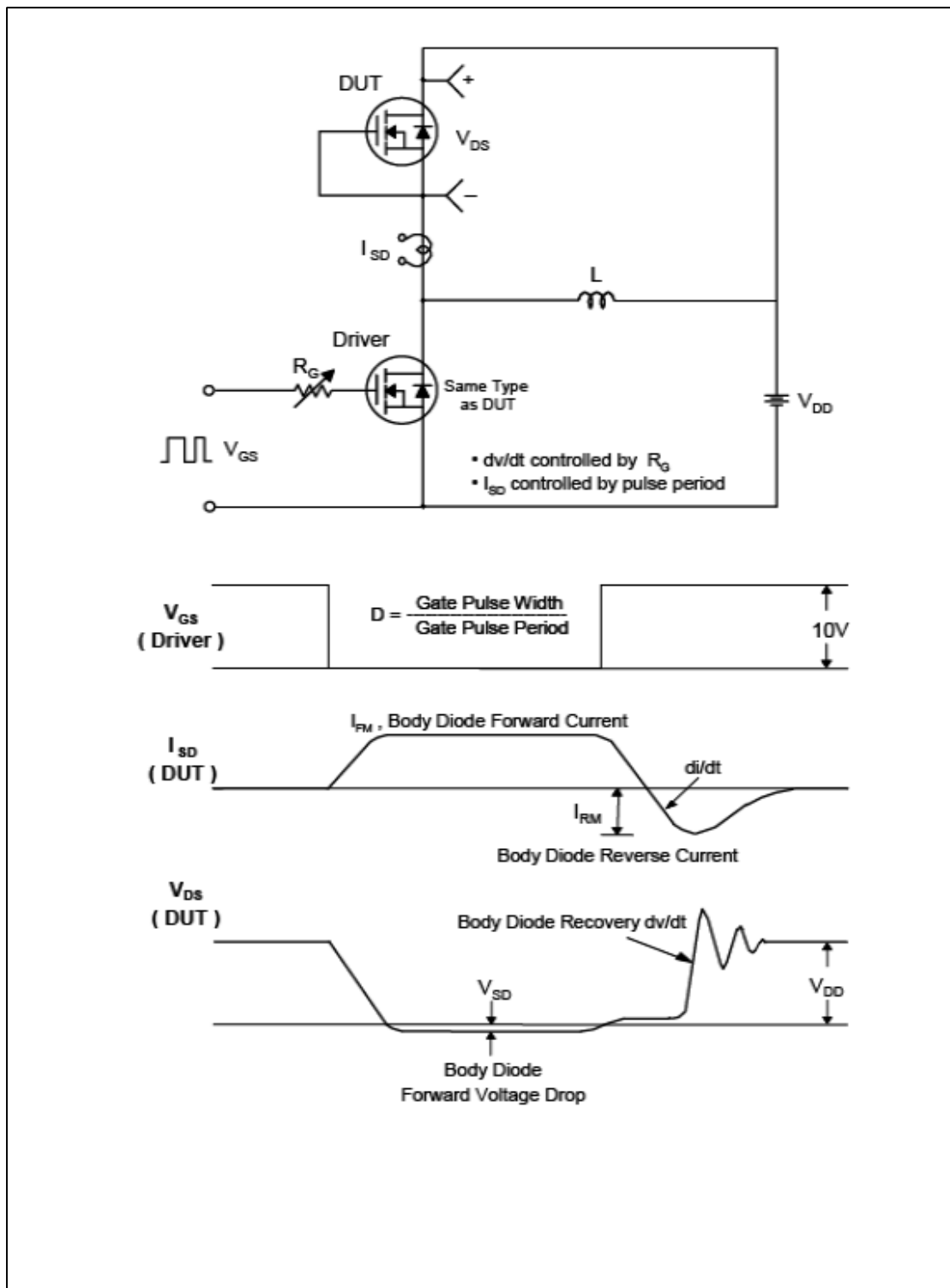


Fig.13 Peak Diode Recovery dv/dt Test Circuit & Waveform

TO-220F Package Dimension

Unit:mm

